

#### COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### **Features & Benefits**

• Complementary Pairs One 2222A Type (NPN)

One 2907A Type (PNP)

- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

Case: SOT363

 Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

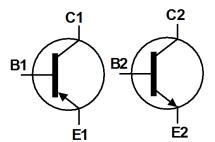
 Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208

Weight: 0.006 grams (approximate)

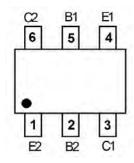








Device Symbol



Top View Pin-Out

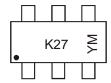
#### Ordering Information (Note 4)

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	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	MMDT2227-7-F	K27	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

#### **Marking Information**



K27 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

#### Date Code Key

Year	2010	20	011	2012	2	2013	2014		2015	2016		2017
Code	Χ		Υ	Z		Α	В		С	D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

MMDT2227 Document Number: DS30122 Rev: 12 - 2 1 of 6

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# Maximum Ratings, 2222A Type (NPN) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	75	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Continuous Collector Current	lc	600	mA

# Maximum Ratings, 2907A Type (PNP) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6.0	V
Continuous Collector Current	Ic	-600	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Notes 5)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	150	-C/VV	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

<sup>5.</sup> Device mounted on 1 inch x 0.85 inch x 0.062 inch FR-4 PCB

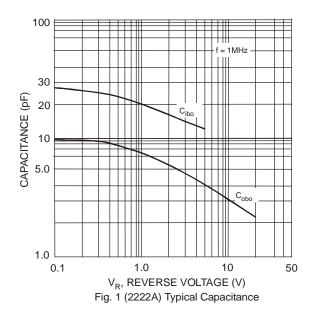
<sup>6.</sup> Thermal resistance from junction to the top of package

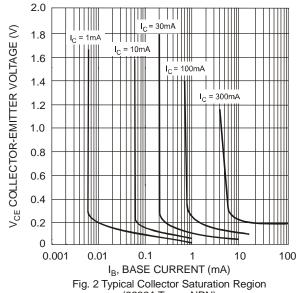


# Electrical Characteristics, 2222A Type (NPN) (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	75	_	V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40		V	$I_C = 10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0		V	$I_E = 100 \mu A, I_C = 0$	
Collector Cutoff Current	Ісво		10	nA μA	$V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0, T_{A} = +150^{\circ}C$	
Collector Cutoff Current	I <sub>CEX</sub>	_	10	nA	$V_{CE} = 60V, V_{EB(off)} = 3.0V$	
Emitter Cutoff Current	I <sub>EBO</sub>		10	nA	V <sub>EB</sub> = 5.0V, I <sub>C</sub> = 0	
Base Cutoff Current	I <sub>BL</sub>	_	20	nA	$V_{CE} = 60V, V_{EB(off)} = 3.0V$	
ON CHARACTERISTICS (Note 7)					, , , , , , , , , , , , , , , , , , ,	
DC Current Gain	h <sub>FE</sub>	35 50 75 100 40 50 35	300	_	$\begin{array}{ll} I_{C} = 100 \mu A, \ V_{CE} = 10 V \\ I_{C} = 1.0 mA, \ V_{CE} = 10 V \\ I_{C} = 10 mA, \ V_{CE} = 10 V \\ I_{C} = 150 mA, \ V_{CE} = 10 V \\ I_{C} = 500 mA, \ V_{CE} = 10 V \\ I_{C} = 10 mA, \ V_{CE} = 10 V, \ T_{A} = -55 ^{\circ} C \\ I_{C} = 150 mA, \ V_{CE} = 1.0 V \end{array}$	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	0.3 1.0	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.6	1.2 2.0	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>		8	pF	$V_{CB} = 10V, f = 1.0MHz, I_{E} = 0$	
Input Capacitance	C <sub>ibo</sub>	_	25	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$	
Current Gain-Bandwidth Product	f⊤	300		MHz	$V_{CE} = 20V$ , $I_C = 20mA$ , $f = 100MHz$	
Noise Figure	NF		4.0	dB	$V_{CE} = 10V, I_{C} = 100\mu A,$ $R_{S} = 1.0k\Omega, f = 1.0kHz$	
SWITCHING CHARACTERISTICS						
Delay Time	t <sub>d</sub>		10	ns	$V_{CC} = 30V, I_C = 150mA,$	
Rise Time	t <sub>r</sub>	_	25	ns	$V_{BE(off)} = -0.5V, I_{B1} = 15mA$	
Storage Time	ts	_	225	ns	$V_{CC} = 30V, I_C = 150mA,$	
Fall Time	t <sub>f</sub>	_	60	ns	$I_{B1} = I_{B2} = 15mA$	

7. Pulse test: Pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ . Notes:



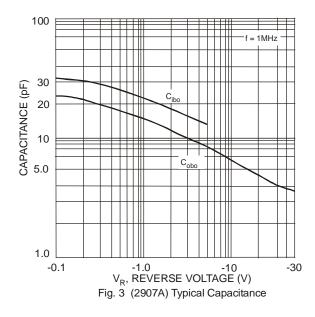


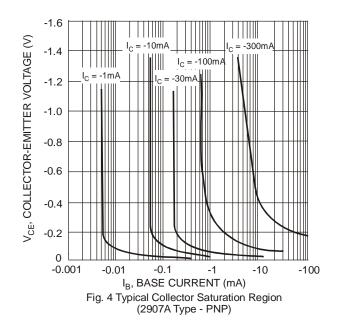


# Electrical Characteristics, 2907A Type (PNP) (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-60		V	$I_C = -100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-60		٧	$I_C = -10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6.0		V	$I_E = -100 \mu A, I_C = 0$	
Collector Cutoff Current	lone		-10	nA	$V_{CB} = -50V, I_{E} = 0$	
	Ісво			μΑ	$V_{CB} = -50V, I_E = 0, T_A = +125^{\circ}C$	
Collector Cutoff Current	I <sub>CEX</sub>		-50	nA	$V_{CE} = -30V, V_{EB(off)} = -0.5V$	
Base Cutoff Current	$I_{BL}$	_	-50	nA	$V_{CE} = -30V, V_{EB(off)} = -0.5V$	
ON CHARACTERISTICS (Note 8)						
		75	_		$I_C = -100 \mu A, V_{CE} = -10 V$	
	h <sub>FE</sub>	100	_	_	$I_C = -1.0 \text{mA}, V_{CE} = -10 \text{V}$	
DC Current Gain		100	_		$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$	
		100	300		$I_C = -150 \text{mA}, V_{CE} = -10 \text{V}$	
		50			$I_C = -500 \text{mA}, V_{CE} = -10 \text{V}$	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	-0.4	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$	
Collector-Emitter Saturation Voltage			-1.6		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		-1.3	V	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$	
	VBE(sat)		-2.6	v	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>		8.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$	
Input Capacitance	C <sub>ibo</sub>	_	30	pF	$V_{EB} = -2.0V$ , $f = 1.0MHz$ , $I_{C} = 0$	
Current Gain-Bandwidth Product	f <sub>T</sub>	200		MHz	$V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS						
Turn-On Time	t <sub>on</sub>		45	ns	_	
Delay Time	t <sub>d</sub>	_	10	ns	$V_{CC} = -30V, I_{C} = -150mA,$	
Rise Time	t <sub>r</sub>		40	ns	$I_{B1} = -15 \text{mA}$	
Turn-Off Time	t <sub>off</sub>	_	100	ns	_	
Storage Time	t <sub>s</sub>		80	ns	$V_{CC} = -6.0V$ , $I_{C} = -150mA$ ,	
Fall Time	t <sub>f</sub>		30	ns	$I_{B1} = I_{B2} = -15 \text{mA}$	

Notes: 8. Short duration pulse test used to minimize self-heating effect.

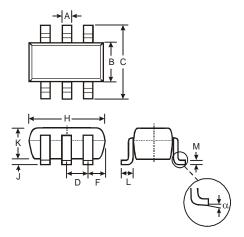






# **Package Outline Dimensions**

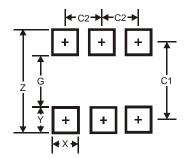
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT363								
Dim	Min	Max	Тур						
Α	0.10	0.30	0.25						
В	1.15	1.35	1.30						
С	2.00	2.20	2.10						
D	0.65 Typ								
F	0.40	0.45	0.425						
Н	1.80 2.20		2.15						
J	0	0.10	0.05						
K	0.90	1.00	1.00						
L	0.25	0.40	0.30						
M	0.10	0.22	0.11						
α	0°	8°	-						
All	Dimen	sions i	n mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

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